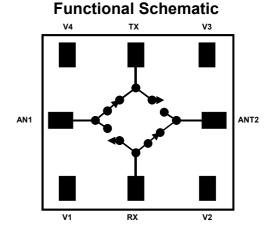


2.4GHz DPDT GaAs Single-Band WLAN Switch

Features:

- ♦ Available as RF known good die
- Suitable for Single-band WLAN 802.11b/g Applications
- ◆ Excellent low control voltage performance
- ♦ Very low Insertion loss typ. 0.55dB at 2.4GHz
- ♦ High isolation typ. 23dB at 2.4GHz



Description and Applications:

The FMS2017 is a low loss, single band Gallium Arsenide antenna diversity switch designed for use in Wireless LAN applications. The die is fabricated using the Filtronic FL05 $0.5\mu m$ switch process technology that offers leading edge performance, optimised for switch applications. The FMS2017 is designed for use in 802.11b/g WLAN modules.

Electrical Specifications: $(T_{AMBIENT} = 25^{\circ}C, V_{ctrl} = 0V/(2.4V, +3.3V), Z_{IN} = Z_{OUT} = 50\Omega)$

| Parameter | Conditions | Min | Тур | Max | Units |
|----------------------------|----------------------------------|-----|------|-----|-------|
| Insertion Loss (All Paths) | 2.5GHz, Small Signal | | 0.55 | | dB |
| Isolation (All Paths) | 2.5GHz, Small Signal | | 23 | | dB |
| Return Loss | 2.5GHz, Small Signal | | 20 | | dB |
| P1dB | 2.5GHz Control Voltage 3.0V | | 37 | | dBm |
| 2nd Harmonic Level | 2.4GHz, Pin = 32dBm, Vctrl =2.4V | | -65 | | dBc |
| 3rd Harmonic Level | 2.4GHz, Pin = 32dBm, Vctrl =2.4V | | -65 | | dBc |
| Switching speed | Vctrl=2.4V, Pin=20dBm | | 20 | | nS |

Note: External DC blocking capacitors are required on all RF ports (typ: 47pF) All unused ports terminated in 50Ω .

Absolute Maximum Ratings:

| Parameter | Symbol | Absolute Maximum |
|-----------------------|--------|------------------|
| Max Input Power | Pin | +36dBm |
| Control Voltage | Vctrl | +5V |
| Operating Temperature | Toper | -40°C to +100°C |
| Storage Temperature | Tstor | -55°C to +150°C |

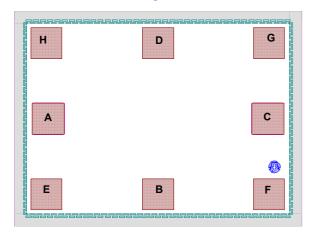
Note: Exceeding any one of these absolute maximum ratings may cause permanent damage to the device.

Truth Table:

| State | V1 | V2 | V3 | V4 | PATH(S) |
|-------|------|------|------|------|-------------------|
| 1 | High | Low | Low | Low | RX-ANT1 |
| 2 | Low | High | Low | Low | RX-ANT2 |
| 3 | Low | Low | High | Low | TX-ANT2 |
| 4 | Low | Low | Low | High | TX-ANT1 |
| 5 | Low | High | Low | High | TX-ANT1 & RX-ANT2 |
| 6 | High | Low | High | Low | TX-ANT2 & RX-ANT1 |

Note: 'High' = +2.4V to +3.3V'Low' = 0V to +0.2V

Pad and Die Layout:



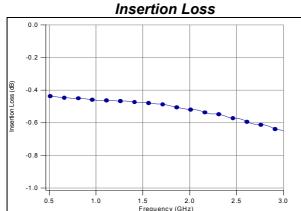
| Pad Ref | Pad Name | Description | Pin Coordinates (μm) |
|------------|-------------|-------------------|-------------------------|
| А | ANT1 | Antenna 1 | (155, 300) |
| В | RX | Receive | (465, 90) |
| С | ANT2 | Antenna 2 | (775, 300) |
| D | TX | Transmit | (465, 510) |
| E | V1 | Vctrl1 (A1 to RX) | (155, 90) |
| F | V2 | Vctrl2 (A2 to RX) | (775, 90) |
| G | V3 | Vctrl3 (TX to A2) | (775, 510) |
| Н | V4 | Vctrl4 (A1 to TX) | (155, 510) |

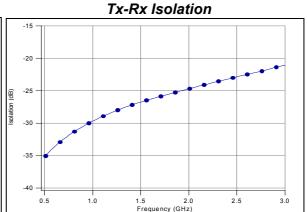
Note: Co-ordinates are referenced from the bottom left hand corner of the die to the centre of the bond pad opening

| Die Size (μm) | Die Thickness (μm) | Min. Bond Pad Pitch (μm) | Min. Bond pad opening (μm) |
|---------------|--------------------|-----------------------------|-------------------------------|
| 930x600 | 150 | 225 | 85x85 |

Typical Measured Performance on Evaluation Board (De-Embedded):

(Measurement Conditions V_{CTRL}=3V, T_{AMBIENT} = 25°C unless otherwise stated)

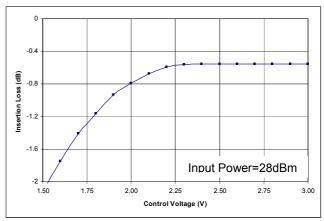




Insertion Loss vs Input Power

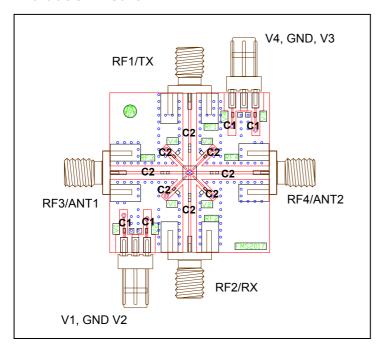


Insertion Loss vs Control Voltage



Website: www.filcs.com

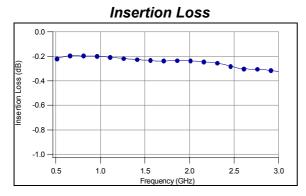
Evaluation Board:

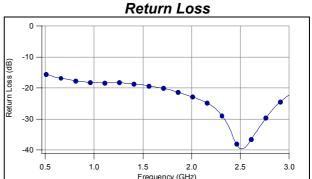


ВОМ

| Label | Component | |
|-------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--|
| C1 | Capacitor, 100pF, 0603 | |
| C2 | Capacitor, 47pF, 0402 | |
| BOARD | Capacitor, 47pF, 0402 Preferred evaluation board material is 0.25 mm thick ROGERS RT4350. All RF tracks should be 50 ohm characteristic impedance. Absolute placement of surface mount de-coupling capacitors is not critical. | |

Evaluation Board De-Embedding Data (Measured):





Ordering Information:

| Part Number | Description |
|----------------|---------------------------------|
| FMS2017-000-WP | Die – waffle pak |
| FMS2017-000-GP | Die – gel pak |
| FMS2017-000-EB | Die mounted on evaluation board |
| FMS2017-000-FF | Wafer mounted on film frame |

Preferred Assembly Instructions:

GaAs devices are fragile and should be handled with great care. Specially designed collets should be used where possible.

The back of the die is not metallised and the recommended mounting method is by the use of conductive epoxy. Epoxy should be applied to the attachment surface uniformly and sparingly to avoid encroachment of epoxy on to the top face of the die and ideally should not exceed half the chip height. For automated dispense Ablestick LMISR4 is recommended and for manual dispense Ablestick 84-1 LMI or 84-1 LMIT are recommended. These should be cured at a temperature of 150°C for 1 hour in an oven especially set aside for epoxy curing only. If possible the curing oven should be flushed with dry nitrogen.

This part has gold (Au) bond pads requiring the use of gold (99.99% pure) bondwire. It is recommended that $25.4\mu m$ diameter gold wire is used. Thermosonic ball bonding is preferred. A nominal stage temperature of $150^{\circ}C$ and a bonding force of 40g has been shown to give effective results for $25\mu m$ wire. Ultrasonic energy shall be kept to a minimum. For this bonding technique, stage temperature should not be raised above 200°C and bond force should not be raised above 60g. Thermosonic wedge bonding and thermocompression wedge bonding can also be used to achieve good wire bonds.

Bonds should be made from the die first and then to the mounting substrate or package. The physical length of the bondwires should be minimised especially when making RF or ground connections.

Handling Precautions:

To avoid damage to the devices care should be exercised during handling. Proper Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. These devices should be treated as Class 1A (0-500 V) as defined in JEDEC Standard No. 22-A114-B. Further information on ESD control measures can be found in MIL-STD-1686 and MIL-HDBK-263.

Disclaimers:

This product is not designed for use in any space based or life sustaining/supporting equipment.